

256K x 4 CMOS Static RAM

Features

- Fast access times: 12*, 15*, 20, 25 ns
- JEDEC-standard pinouts
- Low-power standby when deselected
- TTL-compatible I/O
- 5V $\pm 10\%$ supply
- Fully static operation
- Commercial and industrial temperature ranges
- Packaged in 28-pin, 400-mil SOJ

Functional Description

The Aptos AP9A102A is a high speed, 1-Megabit static RAM organized as a 256K x 4. A fast, efficient design is obtained with a CMOS periphery and a matrix constructed with polysilicon load memory cells.

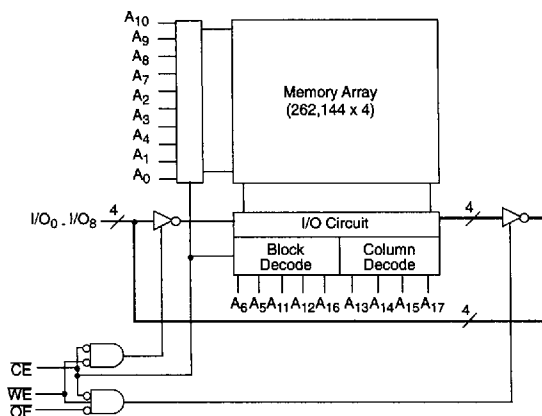
This RAM is fully static in operation. The Chip Enable ($\overline{CE}$) reduces power to the chip when $\overline{CE}$ is HIGH. Standby power drops to its lowest level when $\overline{CE}$ is raised to within 0.2V of V_{CC} .

Write cycles occur when both $\overline{CE}$ and Write Enable ($\overline{WE}$) are LOW. Data is transferred from the I/O pins to the memory location specified by the 18 address lines.

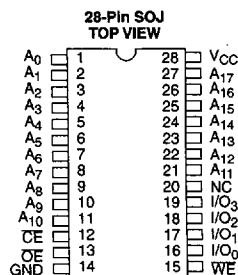
Read cycles occur when $\overline{CE}$ is LOW and $\overline{WE}$ is HIGH. A Read cycle will begin upon an address transition, on a falling edge of $\overline{CE}$, or on a rising edge of $\overline{WE}$.

High-frequency design techniques should be employed to obtain the best performance from this device. Solid, low-impedance power and ground planes, with high-frequency decoupling capacitors, are desirable. Series termination of the inputs should be considered when transmission line effects occur.

Block Diagram



Pin Configuration



Selection Guide

	AP9A102A-12*	AP9A102A-15*	AP9A102A-20	AP9A102A-25
Maximum Access Time (ns)	12	15	20	25
Maximum Operating Current (mA)	165	155	140	125
Maximum Standby Current (mA)	55	50	45	40

*Preliminary

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
V_{CC} Supply Relative to GND

-65° C to +150 ° C
-1.0 V to +7.0 V

Ambient Temperature
Short Circuit Output Current¹
Voltage on any Pin Relative to GND
Power Dissipation

-55°C to +125°C
±50mA
-0.5 to V_{CC}+0.5 V
1.0 W

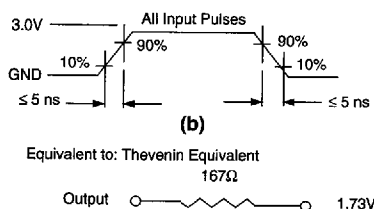
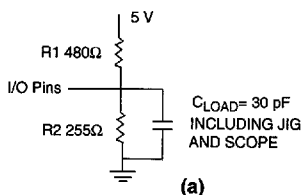
Electrical Characteristics Over the Operating Range (0°C ≤ T_A ≤ 70°C, V_{CC} = 5V ±10%) - Commercial

Symbol	Parameter	Test Conditions	9A102A-12		9A102A-15		9A102A-20		9A102A-25		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I _{CC1}	Operating Current ²	V _{CC} = Max., I _{OUT} = 0 mA, f = f _{MAX.} = 1/t _{RC}		165		155		140		125	mA
I _{SB1}	TTL Standby Current -TTL Inputs	CE ≥ V _{IH} , I _{OUT} = 0		55		50		45		40	mA
I _{SB2}	CMOS Standby Current	CE ≥ V _{CC} - 0.2V, I _{OUT} = 0		10		10		20		10	mA
I _{LI}	Input Leakage Current	V _{IN} = 0V to V _{CC}	-2	2	-2	2	-2	2	-2	2	μA
I _{LO}	Output Leakage Current	V _{IN} = 0V to V _{CC}	-2	2	-2	2	-2	2	-2	2	μA
V _{OH}	Output High Voltage	I _{OH} = -4.0 mA	2.4		2.4		2.4		2.4		V
V _{OL}	Output Low Voltage	I _{OL} = 8.0 mA		0.4		0.4		0.4		0.4	V
V _{IH}	Input High Voltage		2.2	V _{CC} +0.5	2.2	V _{CC} +0.5	2.2	V _{CC} +0.5	2.2	V _{CC} +0.5	V
V _{IL}	Input Low Voltage ³		-0.5	0.8	-0.5	0.8	-0.5	0.8	-0.5	0.8	V

Capacitance^{4, 5}

Symbol	Description	Max.	Unit
C _{IN}	Input Capacitance	7	pF
C _{IO}	I/O Capacitance	8	pF

AC Test Loads and Waveforms



Notes:

1. No more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
2. I_{CC} is dependent upon output loading and cycle rates. Specified values are with outputs open.

3. Negative undershoot of up to 3.0 V is permitted once per cycle.
4. Capacitances are maximum values at 25°C measured at 1 MHz with V_{CC} = 5.0V.
5. Guaranteed but not tested.

Electrical Characteristics Over the Operating Range ($-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, $V_{CC} = 5\text{V} \pm 10\%$) - Industrial

Symbol	Parameter	Test Conditions	9A102A-12		9A102A-15		9A102A-20		9A102A-25		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I_{CC1}	Operating Current ²	$V_{CC} = \text{Max.}, I_{OUT} = 0 \text{ mA}, f = f_{MAX.} = 1/t_{RC}$		190		170		150		140	mA
I_{SB1}	TTL Standby Current -TTL Inputs	$CE \geq V_{IH}, I_{OUT} = 0$		55		55		55		55	mA
I_{SB2}	CMOS Standby Current	$CE \geq V_{CC} - 0.2\text{V}, I_{OUT} = 0$		25		25		25		25	mA
I_{LI}	Input Leakage Current	$V_{IN} = 0\text{V to } V_{CC}$	-2	2	-2	2	-2	2	-2	2	μA
I_{LO}	Output Leakage Current	$V_{IN} = 0\text{V to } V_{CC}$	-2	2	-2	2	-2	2	-2	2	μA
V_{OH}	Output High Voltage	$I_{OH} = -4.0 \text{ mA}$	2.4		2.4		2.4		2.4		V
V_{OL}	Output Low Voltage	$I_{OL} = 8.0 \text{ mA}$		0.4		0.4		0.4		0.4	V
V_{IH}	Input High Voltage		2.2	$V_{CC} + 0.5$	2.2	$V_{CC} + 0.5$	2.2	$V_{CC} + 0.5$	2.2	$V_{CC} + 0.5$	V
V_{IL}	Input Low Voltage ³		-0.5	0.8	-0.5	0.8	-0.5	0.8	-0.5	0.8	V

Switching Characteristics Over the Operating Range ($0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$, $V_{CC} = 5\text{V} \pm 10\%$) ⁷

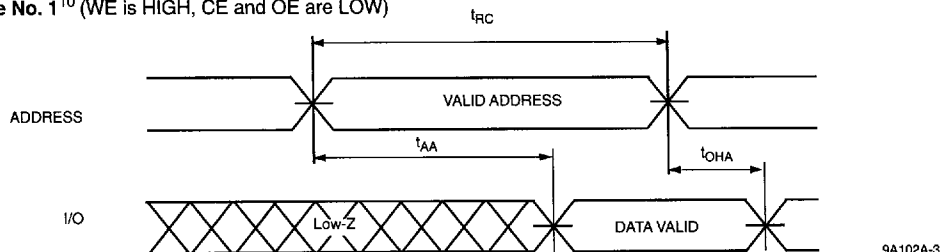
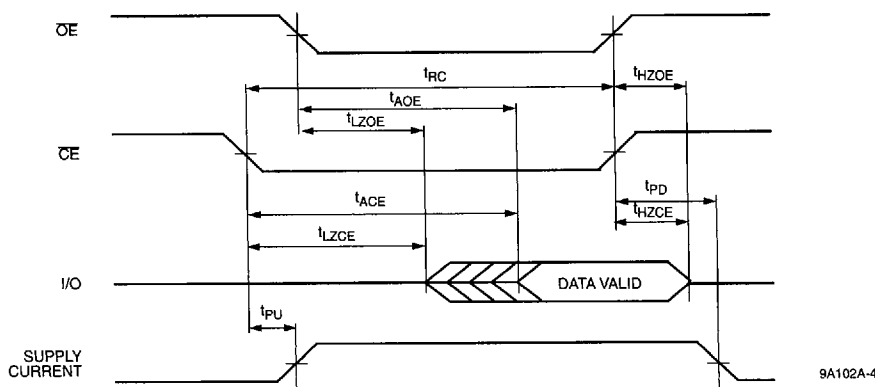
Parameter	Description	9A102A-12		9A102A-15		9A102A-20		9A102A-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t _{RC}	Read Cycle Time	12		15		20		25		ns
t _{AA}	Address Access Time		12		15		20		25	ns
t _{OHA}	Output Hold Time	3		3		3		3		ns
t _{ACE}	CE LOW to Valid Data		12		15		20		25	ns
t _{LZCE}	CE to LOW Output Active ^{8,9}	5		5		5		5		ns
t _{HZCE}	CE to High-Z Output ^{8,9}		8		8		10		15	ns
t _{OEA}	OE LOW to Valid Data		7		7		8		12	ns
t _{LZOE}	OE to Output Active ^{8,9}	0		0		0		0		ns
t _{HZOE}	OE to High-Z Output ^{8,9}		6		6		10		20	ns
t _{PU}	CE to Power Up ⁸	0		0		0		0		ns
t _{PD}	CE to Power Down ⁸		12		15		20		25	ns
Write Cycle										
t _{WC}	Write Cycle Time	12		15		20		25		ns
t _{SCE}	CE LOW to Write End	12		12		15		20		ns
t _{AW}	Address to Set-up Time to Write End	12		12		15		20		ns
t _{HA}	Address Hold to Write End	0		0		0		0		ns
t _{SA}	Address Set-up Time	0		0		0		0		ns
t _{PWE} ⁴	WE Pulse Width	12		12		15		20		ns
t _{SD}	Data Set-up to Write End	9		9		10		12		ns
t _{HD}	Data Hold from Write End	0		0		0		0		ns
t _{HZWE} ²	WE LOW to High-Z Outputs ^{8,9}	0	7	0	8	0	10	0	15	ns
t _{LZWE}	WE HIGH to Low-Z Output ^{8,9}	3		3		3		3		ns

Notes:

7. AC Electrical Characteristics specified at 'AC Test Conditions' levels.

8. Active output-to-High-Z and High-Z-to-output active tests specified to a ± 200 mV transition from steady state levels into the testload. $C_{LOAD} = 5$ pF.

9. Guaranteed but not tested.

Switching Waveforms
Read Cycle No. 1¹⁰ (WE is HIGH, CE and OE are LOW)

Read Cycle No. 2¹¹ (CE is LOW)

Notes:

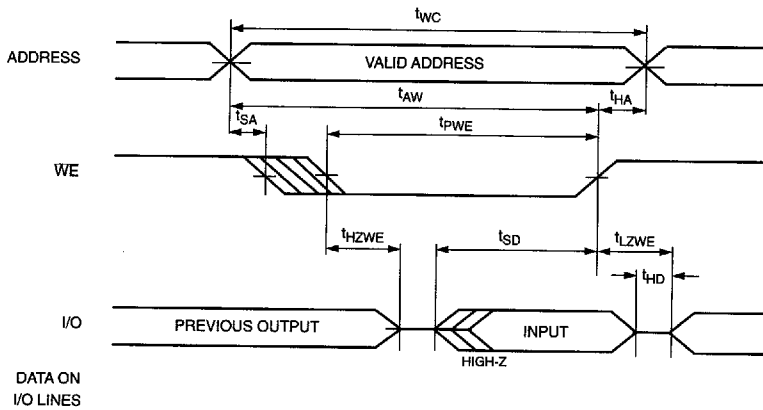
10. Chip is in Read Mode: WE is HIGH, CE and OE are LOW. Read cycle timing is referenced from when all addresses are stable until the first address transition. Crosshatched portion of the I/O implies that

data lines are in the Low-Z state and the data may not be valid.

11. WE is HIGH. I/O is not specified until t_{ACE} , but may become valid as soon as t_{LZCE} . Output will transition from High-Z to valid data out. Data out is valid after both t_{ACE} and t_{AOE} are met.

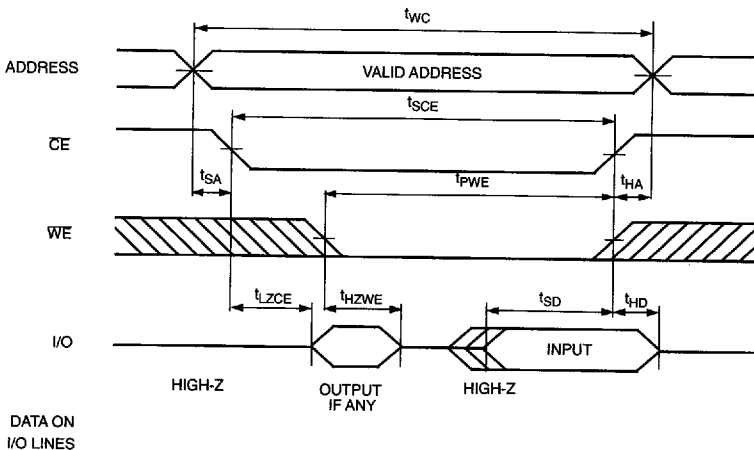
Switching Waveforms (continued)

Write Cycle No. 1 (WE controlled)^{12, 13}



9A102A-5

Write Cycle No.2 (CE controlled)^{12, 14}



9A102A-6

Notes:

12. Addresses must be stable during Write cycles. **CE** or **WE** must be HIGH during address transitions. The outputs will remain in the High-Z state if **WE** is LOW when **CE** goes LOW. Care should be taken so that the output drivers are disabled prior to placing the Input Data on the I/O Lines. This will prevent bus contention, reducing system noise.

13. Chip is selected; **CE** and **OE** are LOW. Using only **WE** to control Write cycles may not offer the best device performance, since both t_{HZWE} and t_{SD} timing specifications must be met.

14. **OE** is LOW. I/O lines may transition to Low-Z if the falling edge of **WE** occurs after the falling edge of **CE**.

Truth Table

Mode	WE	CE	OE	I/O	I _{CC}
Standby	X	H	X	High-Z	Standby
Selected	H	L	H	High-Z	Active
Read	H	L	L	D _{OUT}	Active
Write	L	L	X	D _{IN}	Active

2
Ordering Information

Speed	Part Number	Package Name	Package Type	Temperature Range
12*	AP9A102A-12VC	V28.1	28-Pin Small Outline J-Bend	Commercial
	AP9A102A-12VI	V28.1	28-Pin Small Outline J-Bend	Industrial
15*	AP9A102A-15VC	V28.1	28-Pin Small Outline J-Bend	Commercial
	AP9A102A-15VI	V28.1	28-Pin Small Outline J-Bend	Industrial
20	AP9A102A-20VC	V28.1	28-Pin Small Outline J-Bend	Commercial
	AP9A102A-20VI	V28.1	28-Pin Small Outline J-Bend	Industrial
25	AP9A102A-25VC	V28.1	28-Pin Small Outline J-Bend	Commercial
	AP9A102A-25VI	V28.1	28-Pin Small Outline J-Bend	Industrial

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